

 $4.7k\Omega$ 

2.2kΩ

## **Electronics II**

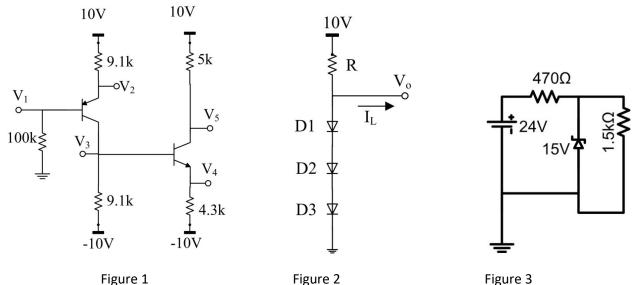
## **Mid Semester Exam 1**

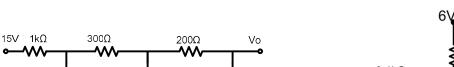
Date: 25<sup>th</sup> February 2015 Time: 90 Minutes Max Marks. 40

Notes: If not mentioned, then use second approximation of diode for problem solving. Marks of each question are mention against it.

Assumptions made should be written clearly.

- Q.1: Design a voltage divider biased Common Emitter configuration BJT amplifier with following specifications. Ic(sat) = 10mA, VCC = 15V, Q point at center of load-line and  $\beta$ dc = 100.
- Q.2: Design a two input OR gate using silicon diodes. You can use current limiter resistors with a maximum value of  $10k\Omega$ . Explain the working and justify the values of resistors used. [5]
- Q.3: For the circuit shown in figure 1, find the labeled node voltages for  $\beta = 100$ . [5]
- Q.4: For the circuit given in figure 2, find the value of resistor R, so that  $V_o = 2.7V$ . Assume that the diodes available have 0.7 Volts drop at 1mA and that  $\Delta V = 0.1V$ /decade change in current. [5]
- Q.5: In figure 3, what is the value of load voltage (Across 1.5kΩ) for each of these cases?
   A: Zener diode shorted
   B: Zener diode open
   C: Series resistor open
   D: Load resistor shorted
   [5]
- Q.6: For the circuit given in figure 4, find the current flowing in each resistor and each diode. [5]
- Q.7: Analyze the circuit given in figure 5 and find out the values of  $r_e$ ,  $I_E$ ,  $V_C$ ,  $V_E$ ,  $A_v$ ,  $f_{Lc1}$ ,  $f_{Lc2}$ ,  $f_{ui}$ , and  $f_{uo}$ . Given Cbc = Cbe = 10pF and  $\beta dc = 100$ . Thus find out 3dB bandwidth of amplifier. [10]





Vz = 5V

 $V_{LED}$  = 2V  $V_{Si}$  Si 0.1kΩ 0.1kΩ 0.2kΩ 0.2kΩ

Figure 4 Figure 5